

MAINTENANCE MANUAL

LB130739B (DF3166) (DF3171, IMT

138—174 MHz, 100/110 WATT POWER AMPLIFIER 19D424583G4 MOBILE 'M'' SERIES & INTERMITTENT DUTY STATION 19D424583G8 MOBILE 'E'' SERIES

19D424786G4 CONTINUOUS DUTY STATION 19D424786G7 CONTINUOUS DUTY DUPLEX

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DESCRIPTION

The modularized 110-Watt PA assembly contains a 10-watt driver module A201, a 110-watt PA module A206, power control circuitry and low pass filter. A total of five transistors, two in the 10-watt driver and three in the 110-watt PA, are used to provide 110-watts RF power for MASTR® II applications and 100-watts for MASTR® Executive II. The output power is adjustable from 20 watts to rated output power and is held constant for normal variations in temperature and voltage.

- CAUTION -

Mobile and Station Power Amplifier Assemblies ARE NOT interchangeable due to different chassis grounding requirements.

However, the individual driver and power amplifier board may be interchanged between mobiles and stations.

Supply voltage for the PA is connected through power leads (from the system-audio-squelch board (SAS) on MASTR Executive II and from the system board on MASTR II) to feedthrough capacitors C297 and C298 on the bottom of the PA assembly. C297, C298, C299, L201 and L202 prevent RF from getting on the power leads. Diode CR295 will cause the main fuse in the fuse assembly to blow

if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

The PA assembly is insulated from vehicle ground to permit operation in positive or negative ground vehicles.

- NOTE -

In positive ground vehicles, A - is "hot" with respect to vehicle ground. Shorting the transmitter PA printed wiring board ground pattern to the radio case may cause one of the inline fuses to blow.

Centralized metering jacks J205 and J210 are provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The Test Set, when connected to J205, meters the Ampl-1 drive (exciter output), power control voltage, Ampl-2 current, and driver current. PA current is metered at J210.

CIRCUIT ANALYSIS

10-WATT DRIVER A201

The exciter output is coupled through an RF cable to PA input jack J201. The RF is coupled through a matching network to the base of Class C amplifier Q1. The network matches the 50-ohm input to the base of Q1 and consists of A201-T1, CA, C5 and C39. R3, C3, R13 and L1 are stablizing networks in the base circuit of Q1.



Part of the RF input is rectified by CR1 and is applied to voltage divider R1 and R2. The voltage is divided to activate the Power Control circuits and for metering the Ampl-1 drive at J205.

Collector voltage to Q1 and Q2 is controlled by the Power Control circuit, and is applied to Q1 through collector stabilizing network L4 and R4 and collector feed network L3 and C6. The collector voltage is metered through R7 at J205-3 (Pos. C).

The output of Q1 is coupled to the base of the second class C amplifier Q2 through a matching network consisting of C10 through C14 and L5 through L7. Collector voltage to Q2 is applied through collector stablizing network L11 and R6 and collector feed network L8 and C15.

The output of the 10-watt driver is taken from the collector of Q2 and applied to the base of PA driver A206-Q1 on the 110-watt PA module through an impedance network, two 50 ohm microstrips, W30, and a second impedance matching network.

The collector impedance matching network for A201-Q2 (L9, L10, C20 and C21), matches the output of Q2 to 50 ohm microstrip A201-W2. C22 is a dc blocking capacitor. W30 interconnects the output of the 10-watt driver (A201-W2) to the input (50 ohm microstrip A206-W1) of the 110-watt PA module.

110-WATT PA MODULE A206

The base impedance matching network (L1-L3, C1-C4 and R1) matches the 50 ohm input impedance to the base of Q1. Collector voltage is coupled through collector stabilizing network Z1 and collector feed network L5 and C5.

Collector current for Q1 is metered across tapped manganin resistor R15 at J205 (Driver Current). The reading is taken on the one-volt scale with the High Sensitivity button pressed and read as 10 amperes full scale.

Following Q1 is a matching network (L4, L21, C7, C57 and C61) that matches the output of Q1 to 50 ohm microstrip W2. The RF energy is then coupled to power divider L6, L7 and Z4 through W2, 50-ohm microstrip W9 and impedance matching network L22, C6 and C62.

The power amplifier stages consist of two identical paralleled Class C PA circuits Q2 and Q3. The output of power divider provides drive for PA transistors Q2 and Q3.

One output of the power divider is applied to the base of Q2 through impedance

matching network C8 through (C11 and L23). L25, L8, C13 and R3 comprise a stabilizing network in the base of Q2. Supply voltage for Q2 is coupled through collector stabilizing network Z2 and collector feed network L10 and C12.

Collector current for Q2 and Q3 is metered across paralleled tapped manganin resistors R12 and R13. The reading is taken on the one-volt scale with the High Sensitivity button pressed, and read as 30 amperes full scale.

The output of Q2 is coupled through matching network L9, L11, C28 and C14-C16 and added to the output of Q3 by power combiner Z5, L12 and L13. The combined output is applied to 50 ohm microstrip W6 through T1 and C56 and is coupled through a low pass filter to the antenna. Capacitors A206-C43 through C54 and A201-C30 through C34 provided isolation for ± ground operation.

- WARNING -

The RF Power Transistors used in the transmitter contain Beryillium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

POWER CONTROL CIRCUIT

The power control circuit, located on the 10-watt driver module and PA Assembly, consists of power control IC A201-U1, thermistor RT201, power adjust A201-R8, pass transistor Q215 and the directional coupler. The power control IC senses the presence of drive power from the exciter, the heat sink temperature, power level, reflected power, and input voltage to provide automatic power leveling across the frequency band.

When the transmitter is keyed, rectified RF from A201-CR1 is applied to pin 10 of U1, turning it on. U1 supplies a reference voltage through pin 4 to power adjust potentiometer A201-R8. The voltage appearing at the arm of R8 is applied back to pin 2 of U1. This voltage determines the base voltage of Q215. The conduction of Q215 sets the collector voltage for 10-watt drivers A201-Q1 and Q2, thereby controlling the RF drive to the PA. The RF output power varies in direct proportion to the RF drive applied to the PA and can be adjusted from approximately 22 to 100-watts for MASTR Executive II and 22 to 110-watts for MASTR II.

- CAUTION -

Due to the reduced heat dissipation capability of the MASTR Executive II heat sink assembly, the MASTR Executive II transmitter should not be adjusted above 100 watts RF output.

Once the power is set to the desired level, UI compares the setting of power adjust control R8 to the actual output power flowing through the directional coupler and adjusts the collector voltage on the 10-watt driver transistors accordingly. A206-CR1 rectifies the sensed forward power from the directional coupler and A206-R6 sets the forward power reference voltage applied to pin of U1.

Reflected power is sensed by the directional coupler and rectified by A206-CR2. When the reflected power exceeds a preset level established by A206-R7, a dc voltage proportional to the reflected power is applied to pin 3 of Ul. Ul lowers the base voltage of Q215, which in turn lowers the collector voltage of the 10-watt driver transistors, thereby reducing transmitter output power.

Temperature protection is provided by U1 and thermistor RT201. RT201 is mounted

on the heat sink assembly. Under normal operating conditions, the temperature sensing circuit is inactive. When the heat sink temperature reaches approximately 100°C , the resistance of RT101 decreases, decreasing the base voltage of Q215. This in turn reduces the collector voltage applied to the 10-watt driver transistors, reducing the transmitter output until at approximately 125°C the output is almost zero. As the temperature of the heat sink decreases the output power increases until full power returns at approximately 100°C .

Overvoltage protection for the RF transistors is also provided by Ul. Should the supply voltage exceed approximately 18 volts, Ul will switch off the collector voltage to the driver transistors, turning them off. The IC will hold the driver transistors off until the supply voltage is reduced to a safe level.

--- CAUTION -

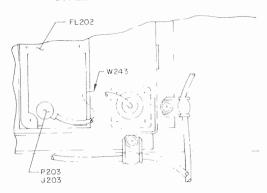
Ul may be damaged if output terminals 12 or 14 are shorted to ground. Use extreme caution when servicing the power control circuit.

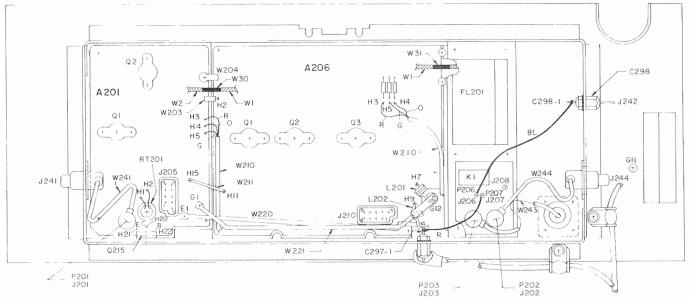
GENERAL ELECTRIC COMPANY+ MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS+LYNCHBURG, VIRGINIA 74502 U.S.A.

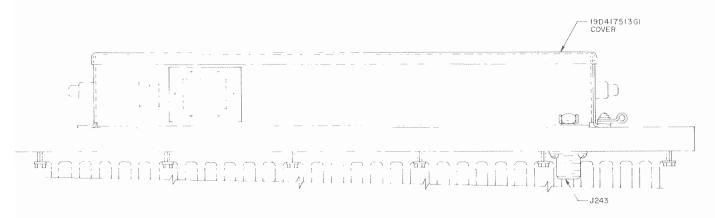


CONTINUOUS DUTY & DUPLEX STATION

DUPLEX STATIONS







(19D429710, Rev. 0)

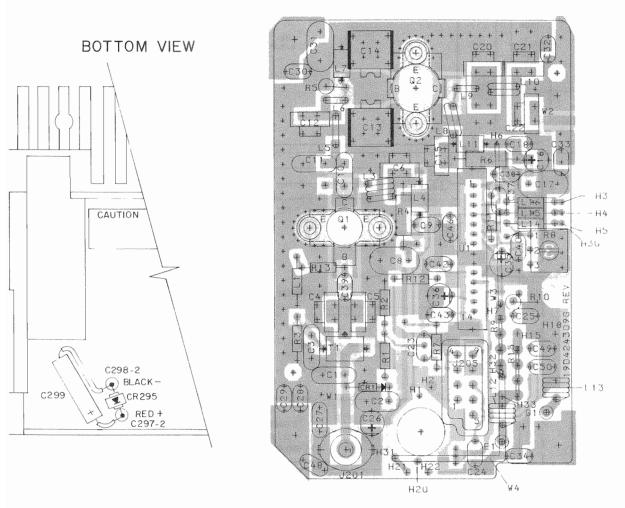
OUTLINE DIAGRAM

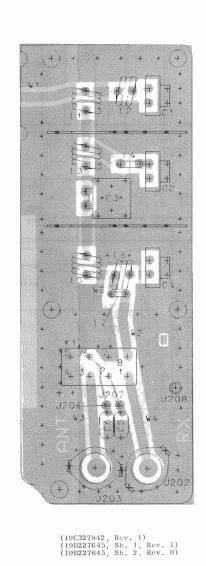
138—174 MHZ POWER AMPLIFIER ASSEMBLIES MOBILE AND STATION

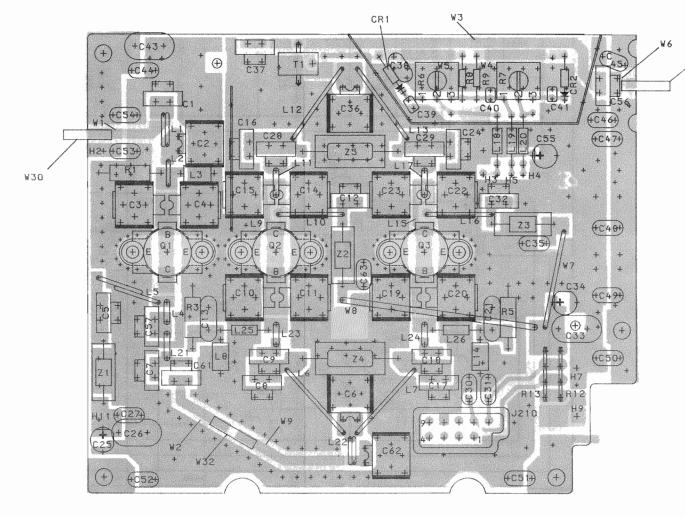
10-WATT DRIVER A201

FL20I

IIO-WATT PA A206







(19C327814, Rev. 4) (19B227604, Sh. 1, Rev. 3) (19B227604, Sh. 2, Rev. 4)

(19D424879, Rev. 8) (19B227634, Sh. 1, Rev. 4) (19B227634, Sh. 2, Rev. 3)

RUNS ON SOLDER SIDE RUNS ON BOTH SIDES RUNS ON COMPONENT SIDE

OUTLINE DIAGRAMS

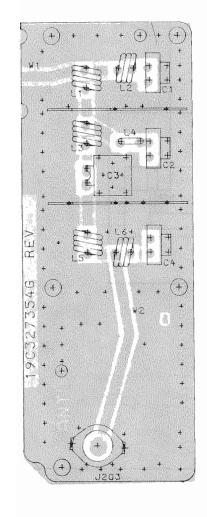
138—174 MHz POWER AMPLIFIER ASSEMBLIES MOBILE & STATION

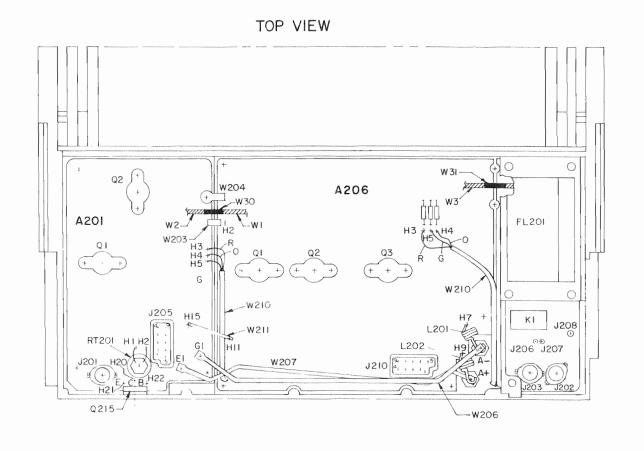
10-WATT DRIVER AZ

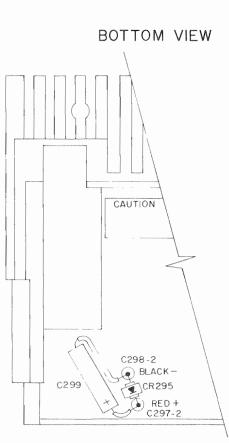
FL202

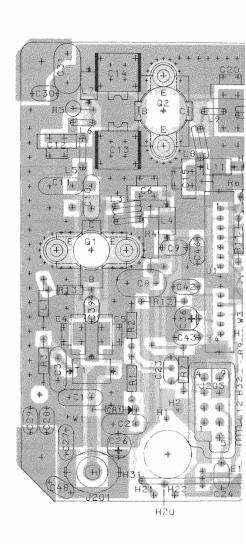
MOBILE & INT. DUTY STATION

(19D429493, Rev. 0)



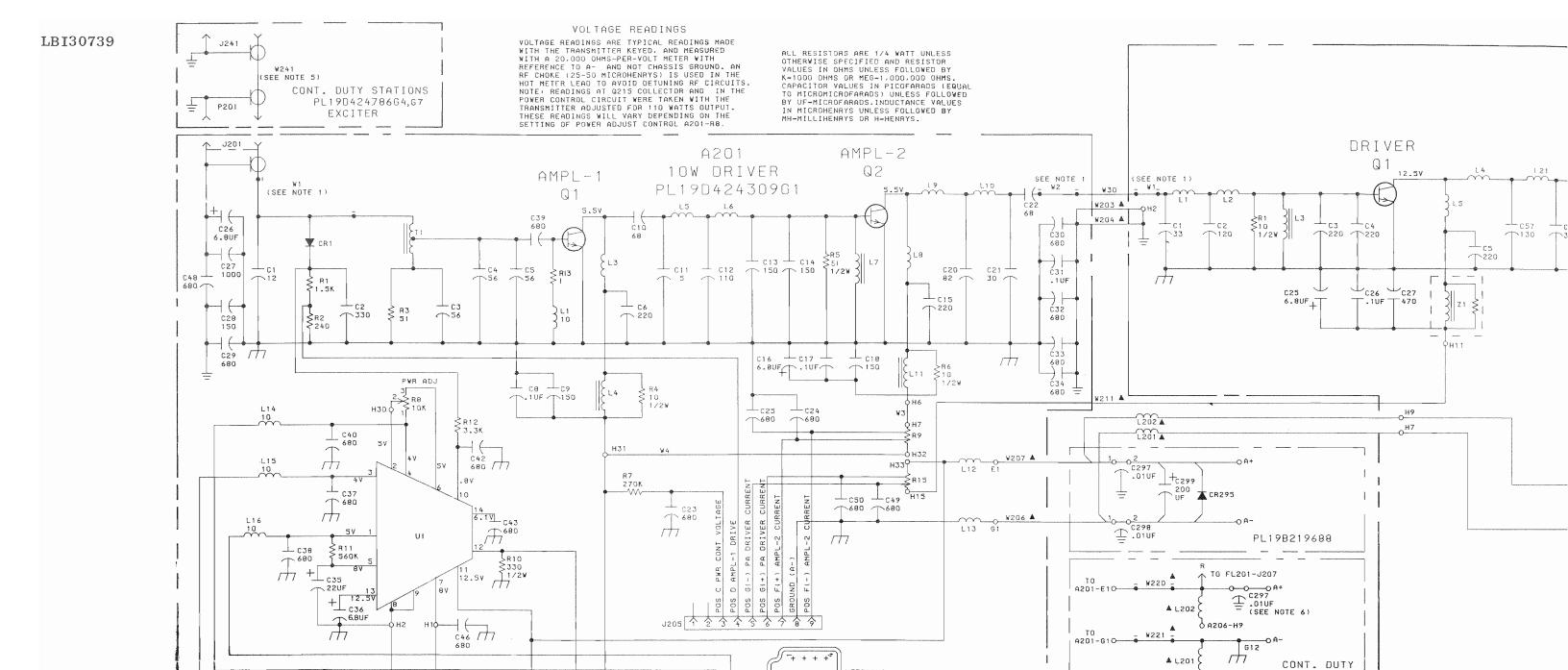






(19C327841, Rev. 1) (19B227651, Sh. 1, Rev. 0) (19B227651, Sh. 2, Rev. 0)





QH22 QH21

Q215 A

METERING JACKS

H5 G

H4 O

0 A206-H7

H

STATIONS

6 O H5

0 O H4

(19R6222

PLI9D424786G4,G7

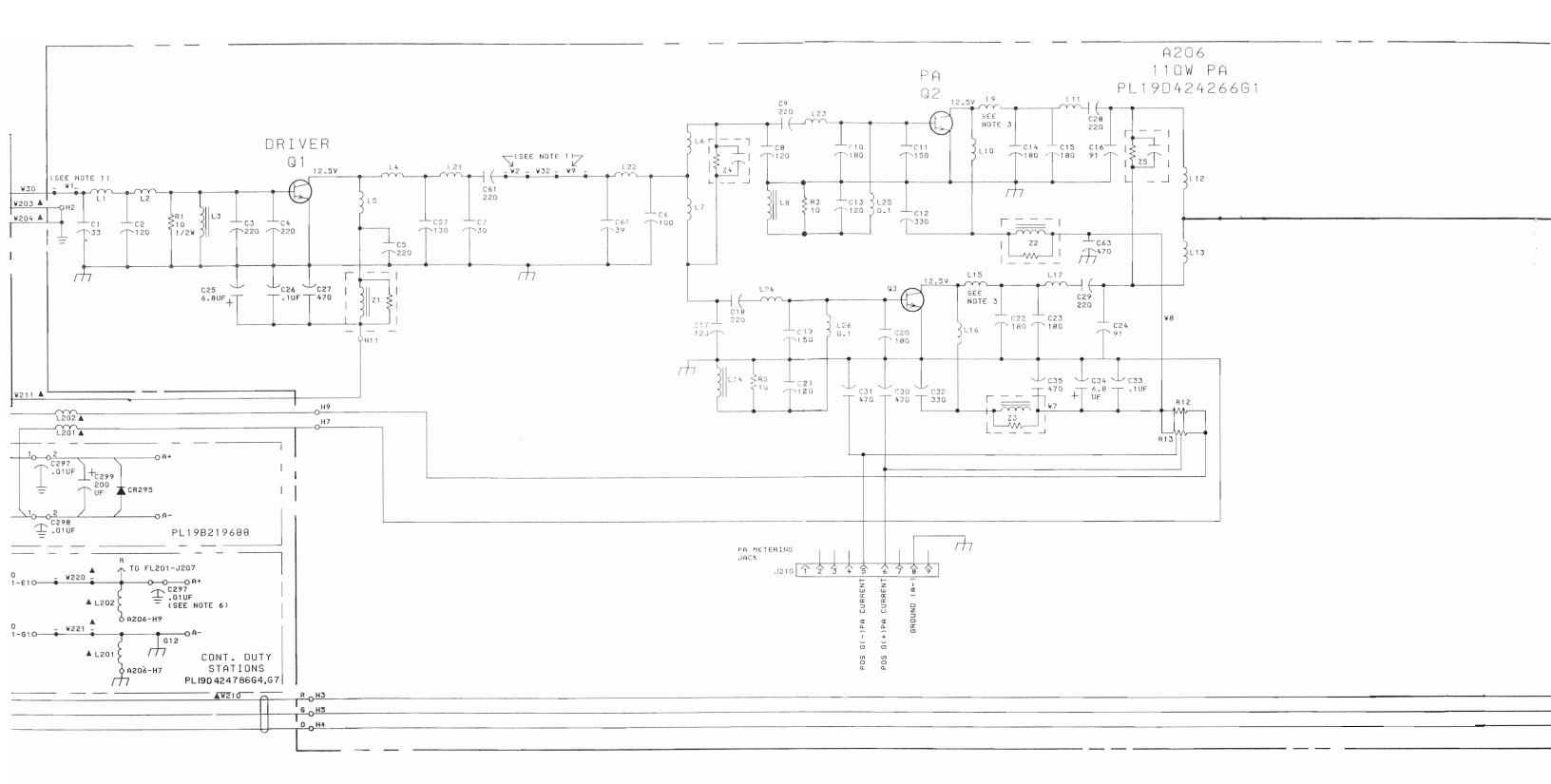
SCHEMATIC DIAGRAM

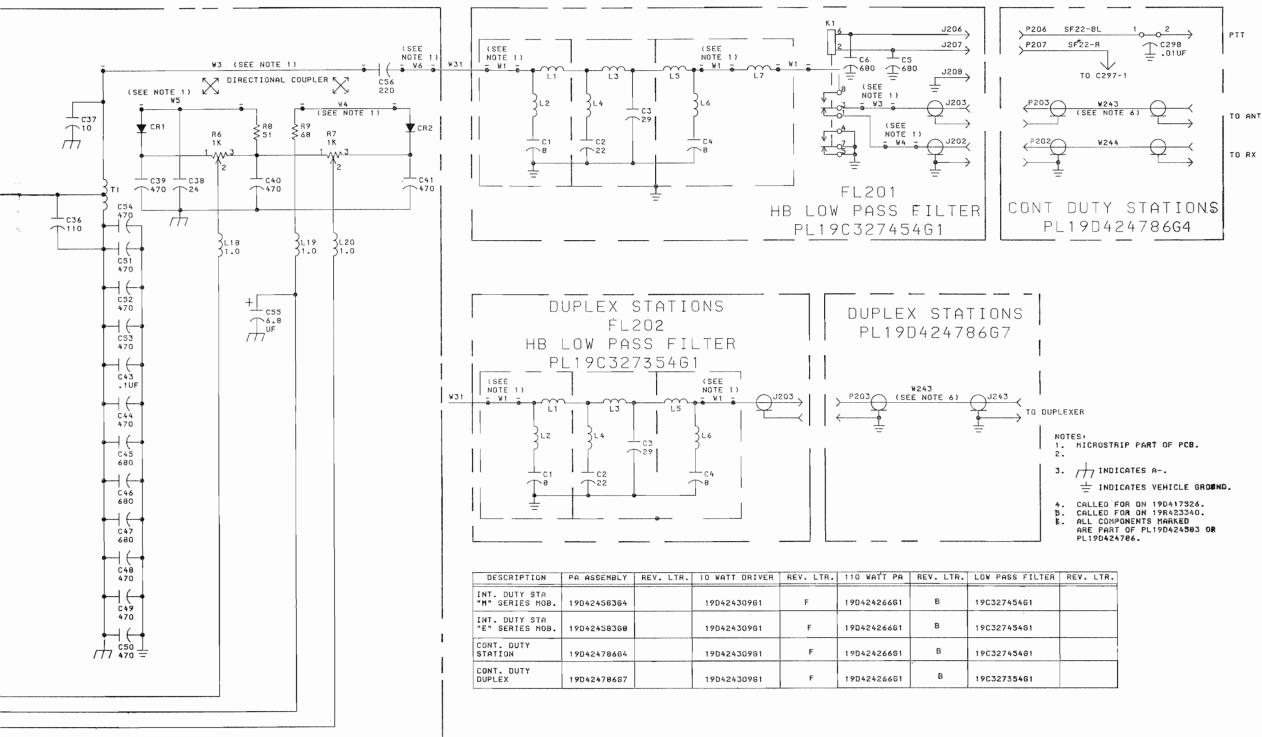
138—174 MHz, 110-WATT POWER AMPLIFIER MOBILE AND STATION

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Issue 3

RT201





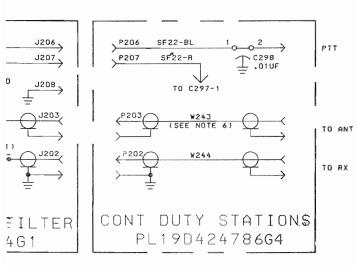
(19R622291, Rev. 13)

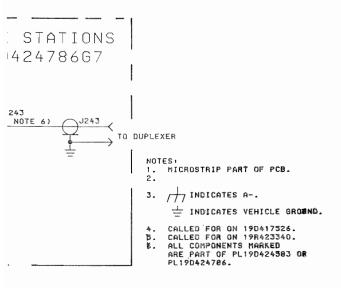
PARTS LIST

138-174 MHz POWER AMPLIFIER ASSEMBLIES 19D424583G1-G8 ISSUE 4

ANT	SYMBOL	GE PART NO.	DESCRIPTION
RX			19D424583G1 25 WATT "M" SERIES MARINE 19D424583G2 40 WATT "M" SERIES MOBILE & INT. DUTY STATION 19D424583G3 65 WATT "M" SERIES MOBILE & INT. 19D424583G4 110 WATT "M" SERIES MOBILE & INT. 19D424583G5 25 WATT "E" SERIES MARINE 19D424583G6 40 WATT "E" SERIES MOBILE 19D424583G7 65 WATT "E" SERIES MOBILE 19D424583G8 110 WATT "E" SERIES MOBILE 19D424583G8 110 WATT "E" SERIES MOBILE
	A201	19D424309G1	10 Watt Driver. (Used with 19D424583G2,G4,G6
	A202	19D42430 9 G3	25 Watt Driver/PA. (Used with 19D424583G1,G3,G7).
	A203	19D424328G1	Coupler. (Used with 19D424583G1, G5).
	A204	19D424872G1	40 Watt Power Amplifier. (Used with 19D424583 G6).
	A205	19D424872G2	65 Watt Power Amplifier. (Used with 19D424583 G7).
	A206	19D424266G1	110 Watt Power Amplifier. (Used with 19D42458 G8).
	FL201		COMPONENT BOARD 19C327454G1
		104112222	Motollized toflon: 8 pf 5 pf 250 VDCW
	C1	19A116679P8D 19A700015P12	Metallized teflon: 8 pf .5 pf, 250 VDCW. Teflon/mica: 22 pf ±5%, 250 VDCW.
	C2 C3	19A700015P12 19A116795P29J	Metallized teflon: 29 pf ±5%, 250 VDCW.
	C4	19A116679P8D	Metallized teflon: 8 pf .5 pf, 250 VDCW.
	C5 and C6	19A116655P18	Ceramic disc: 680 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
	J202 and J203	19A130924G1	JACKS AND RECEPTACLES Connector, receptacle: coaxial, jack type; si to Cinch 14H11613.
	J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071
	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
	к1	19B209558P1	Hermetic sealed: 180 to 341 ohms coil res, 2 C contacts, 8.0 to 16.3 VDC; sim to GE 3SAV176
	L1	19A129569P1	Coil.
	L2	19A129570P1	Coil.
	L3	19A129569PI	Coil.
	L5	19A129575P1 19A129569P1	Coil.
	L5 L6	19A129569P1 19A129570P1	Coil.
	L7	19A136907P1	Coil.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHA





REV. LTR.	LOW PASS FILTER	REV. LTR.
В	19032745461	
В	19032745461	
В	19032745461	
В	19032735461	

PARTS LIST

138-174 MHz POWER AMPLIFIER ASSEMBLIES 19D424583G1-G8

SYMBOL	GE PART NO.	DESCRIPTION	
		19D424583G1 25 WATT "M" SERIES MARINE 19D424583G2 40 WATT "M" SERIES MOBILE ≈ INT. DUTY STATION 19D424583G3 65 WATT "M" SERIES MOBILE ≈ INT. DUTY STATION 19D424583G4 110 WATT "M" SERIES MOBILE ≈ INT. DUTY STATION 19D424583G5 25 WATT "E" SERIES MARINE 19D424583G6 40 WATT "E" SERIES MOBILE 19D424583G7 65 WATT "E" SERIES MOBILE 19D424583G8 110 WATT "E" SERIES MOBILE	
A201	19D424309G1	10 Watt Driver. (Used with 19D424583G2,G4,G6 & G8	
A202	19D424309G3	25 Watt Driver/PA. (Used with 19D424583G1,G3,G5,G7).	
A203	19D424328G1	Coupler. (Used with 190424583G1, G5).	
A204	19D424872G1	40 Watt Power Amplifier. (Used with 19D424583G2, G6).	
A205	19D424872G2	65 Watt Power Amplifier. (Used with 19D424583G3, G7).	
A206	19D424266G1	110 Watt Power Amplifier. (Used with 19D424583G4, G8).	
FL201			
Cl	19A116679P8D	Metallized teflon: 8 pf ,5 pf, 250 VDCW.	
C2	19A700015P12	Teflon/mica: 22 pf ±5%, 250 VDCW.	
C3	19Al16795P29J	Metallized teflon: 29 pf ±5%, 250 VDCW.	
C4	19A116679P8D	Metallized teflon: 8 pf .5 pf, 250 VDCW.	
C5 and C6	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	
J202	19A130924G1		
and J203	19813092401	Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613.	
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.	
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	
к1	19B209558PI	Hermetic sealed: 180 to 341 ohms coil res, 2 form C contacts, 8.0 to 16.3 VDC; sim to GE 3SAV1760A2.	
Ll	19A129569P1	INDUCTORS	
L2	19A129570P1	Coil.	
L3	19A129569PI	Coil.	
L4	19A129575PI	Coil.	
		Coll.	
L5	19A129569P1	Coll.	
	19A129569P1 19A129570P1	Coil.	
L5			

SYMBOL	GE PART NO.	DESCRIPTION
W1 thru W5		(Part of printed board 19D424357P1).
L201 and L202	19A129562P1	Coil.
Q215	19A116742P1	Silicon, NPN.
RT201	19A129379G1	Thermistor: 40K ohms ±20%, color code white; sim to Carborandum Type M08C6J-5.
W203	19A136942P1	Strap.
W204	7878455Pl	Terminal, lug.
W205	19B227912P1	Jumper.
W206	19B227931G3	Jumper.
W207	19B227931G1	Jumper.
W208	19B227074G1	Jumper.
W209	19B226725G1	Jumper.
W210	19B227934G1	Cable: approx 13 inches long.
W211	19A137006P2	Jumper.
		HEAT CINV
		HEAT SINK 19B219688G7 "M" SERIES 19B219688G19 "E" SERIES
		I SHATES
2297 and 2298	19A116708P1	Ceramic, feed-thru: 0.01 μf -0 +100%, 500 VDCW, 20 amp; sim to Erie 327050X5W0103P.
2299	19A115680P10	Electrolytic: 200 µf +150% -10%, 18 VDCW; sim

Rectifier, silicon: 100 VDC blocking, 6 amps.

Insulator, bushing. (Used with Q215).

Insulator. (Located under A201, A202).

Insulator. (Located under A203-A206).

Nameplate. (110 Watt- Located on FL201).

Insulator, plate. (Used with Q215).

Heat sink. ("M" SERIES).

Heat sink. ("E" SERIES).

----- MISCELLANEOUS -----

Nameplate. (25, 40, 65 Watt-Located on FL201).

Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8. (Located between FL201 cover and A203-A206-

Lockwasher, internal tooth: No. 6. (Located between FL201 cover and A203-A206).

Tap screw, Phillips POZIDRIV*: No. 6-32 x 3/4. (Secures FL201 cover).

Machine screw: No. 4-40 x 5/8. (Secures Q1 & Q2 on A201, A202; Q1 on A204, A205; Q1-Q3 on A206).

Machine screw, phillips head: No. 6-32 x 3/8. (Secures A201-A206 boards).

Machine screw: No. $4-40 \times 3/8$. (Used with Q215

Flatwasher: No. 4. (Used with Q215 mounting).

Hex nut: No. 4-40. (Used with Q215 mounting).

19A116783P1

19D416732G7

19D417105G7

19A134016P1

19A116023P3

19C321982P1

19C321442P1

NP280427

NP280428

N404P13C6

19B201074P306

19B201074P312

N44P9010C6

N80P13006C6

N80P9006C6

N402P5C6

7141225P2 19A129434P1

CR295

PARTS LIST

SYMBOL

C48 thru C50 GE PA

19A1166

A201 138-174 MHz, 10 WATT DRIVER 19D424309G1 ISSUE 3

SYMBOL	GE PART NO.	DESCRIPTION	CR1	19A
			23	,,,,
ClA	19A700105P8	Mica: 12 pf ±5%, 500 VDCW.	E1	19A
C2	7489162P39	Silver mica: 330 pf ±5%, 500 VDCm; sim to Electro Motive Type DM-15.	G1	19A
СЗ	19A700105P28	Mica: 56 pf ±5%, 500 VDCW.		
C4A	19A700015P23	Teflon/mica: 56 pf ±5%, 250 VDCW.		
C5A	19A700015P23	Teflon/mica: 56 pf ±5%, 250 vDCw.	J201	19A
C6	19A700015P37	Teflon/mica: 220 pf ±5%, 250 vDCW.	J205	19B
С8	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.		
C9	19A116655P8	Ceramic disc: 150 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	L1	19A
C10A	19A700105P30	Mica: 68 pf ±5%, 500 VDCW.	L2*	19A
C11A*	7489162P101	Silver mica: 5 pf ±.5 pf, 500 VDCW; sim to Electro Motive Type DM-15. Deleted by REV A or B. Added by REV C.	L3A L4	19A
C12	19A700015P30	Teflon/mica: 110 pf ±5%, 250 VDCW.	L5A	19A
C13A	19A700014P33	Teflon/mica: 150 pf ±5%, 250 vDCW.	L6	19A
C14A	19A700014P33	Teflon/mica: 150 pf ±5%, 250 VDCW.	L7	19A
C15	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.	L8A	19A
C16	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.	L9A	19A
			LlOA	1941
C17	19Al16080Pl07	Polyester: 0.1 µf ±10%, 50 VDCW.	L11	19A
C18	19A116655P8	Ceramic disc: 150 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	L12 and	19A1
C20A	19A700015P27	Teflon/mica: 82 pf ±5%, 250 VDCW.	L13	
C21A	19A700015P16	Teflon/mica: 30 pf ±5%, 250 VDCW.	thru	19A7
C22B	19A700015P25	Teflon/mica: 68 pf ±5%, 250 VDCW.	1.16	
C23 thru C25	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	Q1	19A
C26	19A134202P15	Tantalum: 6.8 μf ±20%, 35 VDCW.	Q2A	19A
C27	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.		
C28	19A116655P8	Ceramic disc: 150 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R1 R2	19A7
C29 and C30	19Al16655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R3	19A7
C31	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.	R4	1947
C32 thru C34	19All6655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R5* R5A*	3R77
C35	19A134202P6	Tantalum: 22 μf ±20%, 15 VDCW.	R6	19A7
C36	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.	R7	3R15
C37 and C38	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R8A	19A1
C39*	19All6655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. Deleted by REV A or B. Added by REV C.	R9 R10	19C3
C40	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R11 R12	3R15
C42 and C43	19All6655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	Rl3	19A)
C46	19All6655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R15	190:

PARTS LIST

A201 138-174 MHz, 10 WATT DRIVER 19D424309G1 ISSUE 3

SYMBOL GE PART NO. DESCRIPTION Mica: 12 pf ±5%, 500 VDCW. ClA 19A700105P8 te; sim C2 7489162P39 Silver mica: 330 pf $\pm 5\%$, 500 VDCw; sim to Electro Motive Type DM-15. 19A700105P28 Mica: 56 pf ±5%, 500 VDCW. C3 C4A Teflon/mica: 56 pf ±5%, 250 VDCW. 19A700015P23 C5A 19A700015P23 Teflon/mica: 56 pf $\pm 5\%$, 250 VDCW. C6 19A700015P37 Teflon/mica: 220 pf ±5%, 250 VDCW. C8 19A116080P107 Polyester: 0.1 μf ±10%, 50 VDCW. Ceramic disc: 150 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. C9 19All6655P8 Mica: 68 pf ±5%, 500 VDCW. ClOA 19A700105P30 Silver mica: 5 pf ±.5 pf, 500 VDCW; sim to Electro Motive Type DM-15. Deleted by REV A or B. C11A* 7489162P101 Added by REV C. C12 19A700015P30 Teflon/mica: 110 pf $\pm 5\%$, 250 VDCW. Teflon/mica: 150 pf ±5%, 250 VDCW. C13A 19A700014P33 Teflon/mica: 150 pf $\pm 5\%$, 250 VDCW. C14A 19A700014P33 19A700015P37 Teflon/mica: 220 pf $\pm 5\%$, 250 VDCW. C15 Tantalum: 6.8 μ f $\pm 20\%$, 35 VDCW. C16 19Al34202P15 C17 Polyester: 0.1 μf $\pm 10\%$, 50 VDCW. VDCW. Ceramic disc: 150 pf $\pm 10\%$, 1000 VDCW; sim to 19A116655P8 C18 RMC Type JF Discap. sim C20A 19A700015P27 Teflon/mica: 82 pf $\pm 5\%$, 250 VDCW. Teflon/mica: 30 pf ±5%, 250 VDCW. C21A 19A700015P16 Teflon/mica: 68 pf ±5%, 250 VDCW. C22B 19A700015P25 mps. Ceramic disc: $680~\mathrm{pf}~\pm10\%$, 1000 VDCW; sim to RMC Type JF Discap. 19A116655P18 C23 thru C25 C26 19A134202P15 Tantalum: 6.8 μ f $\pm 20\%$, 35 VDCW. Ceramic disc: 1000 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap. C27 19A116655P19 Ceramic disc: 150 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. C28 19All6655P8 Ceramic disc: 680 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. 19A116655P18 C29 Polyester: 0.1 μ f \pm 10%, 50 VDCW. C31 19A116080P107 L201). Ceramic disc: $680~\mathrm{pf}~\pm10\%$, $1000~\mathrm{VDCW};$ sim to RMC Type JF Discap. C32 19A116655P18 thru C34 Tantalum: 22 µf ±20%, 15 VDCW. C35 19A134202P6 Tantalum: 6.8 μ f $\pm 20\%$, 35 VDCW. C36 19A134202P15 ted Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C37 19Al16655Pl8 3/4. Ceramic disc: 680 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. Deleted by REV A or B. Added by REV C. C39* 19A116655P18 Ceramic disc: 680 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. 3/8. C40 19A116655P18 Ceramic disc: $680~\text{pf}~\pm10\%$, 1000 VDCW; sim to RMC Type JF Discap. 19A116655P18 C42 ing). Ceramic disc: $680~\mathrm{pf}~\pm10\%$, 1000 VDCW; sim to RMC Type JF Discap. 19A116655P18 C46 ing).

C48 thru		
thm	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to
C50		RMC Type JF Discap.
C51*	19B209723P5	Tantalum: 6.8 μ f $\pm 20\%$, 20 VDCw. Added by REV E. Deleted by REV F.
		DIODES AND RECTIFIERS
CR1	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.
E1	19A13/263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.
G1	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.
ļ		JACKS AND RECEPTACLES
J201	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613.
J205	19B219374G1	Connector: 9 contacts.
L1	19A700024P25	Coil, RF: 10.0 µh ±10%, 3.70 ohms DC res max.
L2*	19A142583Pl	Coil. Added by REV A or B. Deleted by REV C.
L3A	19A136530P1	Coil.
LA	19A129773G1	Coil.
L5A	19A136532P2	Coil.
L6	19A129575Pl	Coil.
L7	19A129773G1	Coil.
L8A	19A129561P1	Coil.
L9A	19A136907P2	Coil.
Lloa	19A129561P1	Coil.
L11	19A129773G1	Coil.
L12 and L13	19A129569P1	Coil.
L14 thru L16	19A700024P25	Coil, RF: 10.0 µh ±10%, 3.70 ohms DC res max.
		TRANSISTORS
Q1	19A134340P1	Silicon, NPN. BVCBO 36 v min; 10 w min at 12.5 v.
Q2A	19A134340P3	Silicon, NPN. BVCBO 36 v min; 25 w min at 12.5 v.
Rl	19A700106P67	
R2	3R152P241J	Composition: 240 ohms ±5%, 1/4 w.
R3	38152P2413 19A700106P32	Composition: 51 ohms ±5%, 1/4 w.
R4	19A700108P32	Composition: 10 ohms £5%, 1/2 w.
R5*	3R77P100J	Composition: 10 ohms ±5%, 1/2 w. Deleted by REV D.
R5A*	19A7U0113P32	Composition: 51 ohms $\pm 5\%$, $1/2$ w. Added by REV D.
R6	19A700113P15	Composition: 10 ohms £5%, 1/2 w.
R7	3R152P274J	Composition: 270K ohms ±5%, 1/4 w.
R8A	19A116559P106	Variable, cermet: 10K ohms $\pm 20 \text{\%}$, 0.5 w; sim to CTS Series 360.
R9	19C320212P2	Shunt resistor.
R10	19A700113P51	Composition: 330 ohms ±5%, 1/2 w.
R11	3R152P564J	Composition: 560K ohms ±5%, 1/4 w.
R12	19A700106P75	Composition: 3.3K ohms ±5%, 1/4 w.
R13	19A1162;6P1ROJ	Deposited carbon: 1.0 ohms ±5%, 1/4 w; sim to Mepco Electra Type CR25.
R15	19C320212P2	Shunt resistor.

SYMBOL	GE PART NO.	DESCRIPTION
		TRANSFORMERS
Т1	19A129564G1	Coil.
U1*	19D429709G3	IC, Power Control. In REY E & earlier:
	19D429709G1	IC, Power Control.
W1 and		(Part of printed board 19D424308P1).
W2 W3	19B227912P1	Jumper.
₩4	198227912P2	Jumper.
		MISCELLANEOUS
	19A136950P1	Strap. (Solders to W2).

SCHEMATIC DIAGRAM

138-174 MHz, 110-WATT POWER AMPLIFIER MOBILE AND STATION

Issue 3

PARTS LIST

138-174 MHz POWER AMPLIVIER ASSEMBLIES 19D424786G2-G7 ISSUE 3

SYMBOL	GE PART NO.	DESCRIPTION	
		19D424786G2 40 WATT CONTINUOUS DUTY STATION 19D424786G4 100 WATT CONTINUOUS DUTY STATION 19D424786G6 100 WATT CONTINUOUS DUTY STATION 19D424786G6 40 WATT CONTINUOUS DUTY DUPLEX STA. 19D424786G6 5 WATT CONTINUOUS DUTY DUPLEX STA. 19D424786G7 100 WATT CONTINUOUS DUTY DUPLEX STA.	
A201	19D424309G1	10 Watt Driver. (Used with 19D424786G2,G4,G5,G7).	
A202	19D424309G3	25 Watt Driver. (Used with 19D424786G3, G6).	
A204	19D424872G1	40 Watt Power Amplifier. (Used with 19D424786G2, G5).	
A205	19D424872G2	65 Watt Power Amplifier. (Used with 19D424786G3, G6).	
A206	19D424266G1	110 Watt Power Amplifier. (Used with 19D424786G4, G7).	
C297 and C298	19A116708P1	Ceramic, feed-thru: 0.01 μf +100½ -0½, 500 VDCW; sim to Erie Style 327.	
FL201		COMPONENT BOARD	
IBBOI		19C327454G1	
Cl	19A116679P8D	Metallized teflon: 8 pf ±.5 pf, 250 VDCW.	
C2	19A700015P12	Teflon/mica: 22 pf ±5%, 250 VDCW.	
C3	19A116795P29J	Metallized teflon: 29 pf ±5%, 250 VDCW.	
C4	19A116679P8D	Metallized teflon: 8 pf ±.5 pf, 250 VDCW.	
C5 and C6	19A116655P18	Ceramic disc: 680 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.	
		JACKS AND RECEPTACLES	
J202 and J203	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H116113.	
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.	
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	
		RELAYS	
K1	19B209558Pl	Hermetic sealed: 180 to 341 ohms coil res, 2 form C contacts, 8.0 to 16.3 VDC; sim to GE 3SAV1760A2.	
Ll	19A129569Pl	Coil.	
L2	19A129570P1	Coil.	
L3	19A129569P1	Coil.	
I.4	19A129575P1	Coil.	
L5	19A129569P1	Coil.	
L6	19A129570Pl	Coil.	
L7	19A126907P1	Coil.	
		1	

SYMBOL	GE PART NO.	DESCRIPTION
		an and a second
W1 thru W5		(Part of printed board 19D424357P1).
FL202		COMPONENT BOARD 19C327354C1
C1	19Al16679P8D	Metallized teflon: 8 pf ±.5 pf, 250 VDCW.
C2	19A700015P12	Teflon/mica: 22 pf ±5% , 250 VDCW.
C3	19A116795P29J	Metallized teflon: 29 pf ±5%, 250 VDCW.
C4	19A116679P8D	Metallized teflon: 8 pf ±.5 pf, 250 VDCW.
		JACKS AND RECEPTACLES
J203	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H116113.
Ll	19A129569P1	Coil.
L2	19A129570P1	Coil.
L3	19A129569P1	Coil.
L4	19A129575P1	Coil.
L5	19A129569P1	Coil.
L6	19A129570P1	Coil.
W1 and		(Part of printed board 19D424362Pl).
		INDUCTORS
L201	19A129562P4	Coil.
L202	19A129562P3	Coil.
P206 and P207	4036634P1	Contact, electrical; sim to AMP 42428-2.
P201		TRANSISTORS
Q215	19A116742P1	Silicon, NPN.
		THERMISTORS
RT201	19A129379G1	Thermistor: 40,000 ohms $\pm 20\%$, color white; sim to Carborundum MO806J-5.
₩203	19A136942P1	Strap.
₩204	7878455P1	Terminal, lug.
W205	19B227912P1	Jumper.
W210	19B227934G1	Cable: approx 13 inches long.
W211	19A137006P2	Jumper.
W220 W221	19B227931G2 19B227931G4	Jumper.
	19022(93164	Jumper.
W243		CABLE ASSEMBLY 19A129312G6
		JACKS AND RECEPTACLES
		Connector. Includes:
J203		Receptacle, coaxial: sim to Amphenol 83-798.
J203	4029493P1	
J203	4029493P1 4029082P2	Cover.
J203		
J203		Cover.

SYMBOL	GE PART NO.	DESCRIPTION
		MISCELLANEOUS
	19A134016P1	Insulator, bushing. (Used with Q215).
	19A116023P3	Insulator, plate. (Used with Q215).
	19C321982P1	Insulator. (Located under A201 & A202).
	19C321442P1	Insulator. (Located under A204-A206).
	19B219404G1	Shield electrical. (Located under FL201 casting)
	19D416275P2	Casting. (FL201).
	19D417513G1	PA cover.
	19B226212G1	Heat sink. (The 3 center heat sinks on 75, 100, 110 WATT & the only 2 heat sinks on the 40, 65
	19B226212G2	WATT power amplifiers). Heat sink. (Located on J243 end on the 75, 100, 110 Watt Power amplifiers Quantity 1).
	19B226212G3	Heat sink. (Located on W241 end on the 75, 100, 110 Watt power amplifiers- Quantity 1).
	7150186P127	Spacer, (Termination for L201 & W221).
	N529P18C6	Button plug. (Used when C298 is not used- Duplex
	4029851P13	Clip loop. (Located near J243- Quantity 2).
	19B209268P113	Terminal, solderless: sim to AMP 2-34835-4. (Solders to C297-2).
	7491823P13	Terminal, solderless. (Used on power ground wire at PA).
	7139898P3	Nut, hex, brass: 1/4-28. (Secures C297 & C298).
	N80P13016C6	Machine screw, phillips head: No. 6-32 x 1. (Secures FL201 casting- Quantity 5).
	19B201074P308	Tap screw, Phillips POZIDRIV [®] : No. 6-32 x $1/2$. (Located between FL201 casting and A204-A206-Grounds FL201 shield).
	N44P9010C6	Machine screw: No. 4-40 x 5/8. (Secures Q1, Q2 on A201 & A202; Q1-Q3 on A204-A206).
	19B201074P320	Tap screw, Phillips POZIDRIV*: No. 6-32 x 1-1/4. (Secures L201 & W221 at spacer).
	19B201074P204	Tap screw, Phillips PO/IDRIV®: No. 4-40 x 1/4. (Secures J243 & J244).
	19B209103P410	Tap screw, hex head: No. 8-32 x 5/8. (Secures heat sinks). Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8.
	1985010145300	(Secures cable clip loops and power ground terminal).

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PARTS LIST

A206 138-174 MHz, 110 WATT POWER AMPLIFIER 190424266G1 ISSUE 3

SYMBOL	GE PART NO.	DESCRIPTION
Cl	19A700015P17	Teflon/mica: 33 pf ±5%, 250 VDCW.
C2	19All6795Pl20J	Silver mica: 120 pf ±5%, 250 VDCW.
C3 and C4	19A700014P37	Teflon/mica: 220 pf ±5%, 250 VDCW; sim
C5	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C6	19A116795P100J	Silver mica: 100 pf ±5%, 250 VDCW.
C7	19A700015P16	Teflon/mica: 30 pf ±5%, 250 VDCW.
C8	19A700015P31	Teflon/mica: 120 pf ±5%, 250 VDCW.
C9	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C10	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C11	19A700014P33	Teflon/mica: 150 pf ±5%, 250 VDCW.
C12	19A700015P41	Teflon/mica: 330 pf ±5%, 250 vDCw.
C13	19A700105P36	Mica: 120 pf ±5%, 500 VDCW.
C14 and C15	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C16	19A700014P28	Teflon/mica: 91 pf ±5%, 250 VDCW.
C17	19A700014P31	Teflon/mica: 120 pf ±5%, 250 VDCW.
617	100000000000000000000000000000000000000	1010H, 1200 P. 200, 100 100 1
C18	19A700014P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C19	19A700014P33	Teflon/mica: 150 pf ±5%, 250 VDCW.
C20	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C21	19A700105P36	Mica: 120 pf ±5%, 500 VDCW.
C22 and C23	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C24	19A700015P28	Teflon/mica: 91 pf ±5%, 250 VDCW.
C25	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.
C26	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
C27	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; to RMC Type JF Discap.
C28 and C29	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C30 and C31	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; to RMC Type JF Discap.
C32	19A700015P41	Teflon/mica: 330 pf ±5%, 250 VDCW.
C33	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
C34	19A134202P15	Tantalum: 6.8 μf ±20%, 35 VDCW.
C35	19A116655P13	Ceramic disc: 470 pf ±20; , 1000 VDCW; to RMC Type JF Discap.
C36	19A116795P110J	Silver mica: 110 pf ±5%, 250 VDCW.
C37	19A700015P4	Teflon/mica: 10 pf ±5%, 250 VDCW.
C38	5496218P648	Ceramic disc: 24 pf ±5%, 500 VDCW, ter coef -470 PPM.
C39 thru C41	19A116192P2	Ceramic: 470 pf ±20%, 50 VDCW; sim to A050-W5R-471M.
	<u> </u>	

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION

DESCRIPTION

---- MISCELLANEOUS ---nsulator, bushing. (Used with Q215).

nsulator, plate. (Used with Q215).

nsulator. (Located under A201 & A202).

nsulator. (Located under A204-A206).

shield electrical. (Located under FL201 casting)

asting. (FL201).

A cover.

leat sink. (The 3 center heat sinks on 75, 100, .10 WATT & the only 2 heat sinks on the 40, 65 ATT power amplifiers).

leat sink. (Located on J243 end on the 75, 100, 10 Watt Power amplifiers Quantity 1).

leat sink. (Located on W241 end on the 75, 100, .10 Watt power amplifiers- Quantity 1).

spacer. (Termination for L201 & W221).

utton plug. (Used when C298 is not used- Duplex).

!lip loop. (Located near J243- Quantity 2).

erminal, solderless: sim to AMP 2-34835-4. Solders to C297-2).

'erminal, solderless. (Used on power ground wire .t ${\tt PA}$).

ut, hex, brass: 1/4-28. (Secures C297 & C298).

Tachine screw, phillips head: No. 6-32 x 1. Secures FL201 casting- Quantity 5).

'ap screw, Phillips POZIDRIV®: No. 6-32 x 1/2. Located between FL201 casting and A204-A206-rounds FL201 shield).

lachine screw: No. 4-40 x 5/8. (Secures Q1, Q2 in A201 & A202; Q1-Q3 on A204-A206).

'ap screw, Phillips POZIDRIV $^{\oplus}$: No. 6-32 x 1-1/4. Secures L201 & W221 at spacer).

'ap screw, Phillips POZIDRIV $^\oplus\colon$ No. 4-40 x 1/4. Secures J243 & J244).

'ap screw, hex head: No. 8-32 x 5/8. (Secures leat sinks).

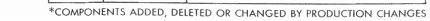
'ap screw, Phillips POZIDRIV $^{\oplus}$: No. 6-32 x 3/8. Secures cable clip loops and power ground :erminal).

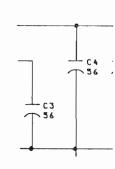
PARTS LIST

A206 138-174 MHz, 110 WATT POWER AMPLIFIER 19D424266G1 1SSUE 3

SYMBOL	GE PART NO.	DESCRIPTION
C1	19A700015P17	Teflon/mica: 33 pf ±5%, 250 VDCW.
C2	19A116795Pl20J	Silver mica: 120 pf ±5%, 250 VDCW.
C3 and C4	19A700014P37	Teflon/mica: 220 pf ±5%, 250 VDCW; sim to
C5	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C6	19A116795P100J	Silver mica: 100 pf ±5%, 250 VDCW.
C7	19A700015P16	Teflon/mica: 30 pf ±5%, 250 VDCW.
C8	19A700015P31	Teflon/mica: 120 pf ±5%, 250 VDCW.
C9	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C10	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C11	19A700014P33	Teflon/mica: 150 pf ±5%, 250 VDCW.
C12	19A700015P41	Teflon/mica: 330 pf ±5%, 250 VDCW.
C13	19A700105P36	Mica: 120 pf ±5%, 500 VDCW.
C14 and C15	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C16	19A700014P28	Teflon/mica: 91 pf ±5%, 250 VDCW.
C17	19A700014P31	Teflon/mica: 120 pf ±5%, 250 VDCW.
C18	19A700014P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C19	19A700014P33	Teflon/mica: 150 pf ±5%, 250 VDCW.
C20	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C21	19A700105P36	Mica: 120 pf ±5%, 500 VDCW.
C22 and C23	19A700014P35	Teflon/mica: 180 pf ±5%, 250 VDCW.
C24	19A700015P28	Teflon/mica: 91 pf ±5%, 250 VDCW.
C25	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.
C26	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
C27	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C28 and C29	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.
C30 and C31	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C32	19A700015P41	Teflon/mica: 330 pf ±5%, 250 VDCW.
C33	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
C34	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.
C35	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C36	19A116795P110J	Silver mica: 110 pf ±5%, 250 VDCW.
C37	19A700015P4	Teflon/mica: 10 pf ±5%, 250 VDCW.
C38	5496218P648	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -470 PPM.
C39 thru	19A116192P2	Ceramic: 470 pf $\pm 20\%$, 50 VDCW; sim to Erie 11-A050-W5R-471M.

	SYMBOL	GE PART NO.	DESCRIPTION	CONTRACTOR COMMANDE	SYMBOL	GE PART NO.	DESCRIPTION
	C43	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.				RESISTORS
	C44	19A116655P13	Ceramic disc: 470 pf +20%, 1000 VDCW: sim		Rl	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
	C45	19A116655P18	to RMC Type JF Discap. Ceramic disc: 680 pf ±10%, 1000 VDCW; sim		R3	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
	thru C47	23/11/00/07/10	to RMC Type JF Discap.		R5	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
	C48 thru C54	19A116655P13	Ceramic disc: 470 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.		R6 and R7	19All6559P101	Variable, cermet: lK ohms $\pm 20\%$, 0.5 w; sim to CTS Series 360.
	C55	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.		R8	19A700106P32	Composition: 51 ohms ±5%, 1/4 w.
	C56	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.		R9	19A700106P35	Composition: 68 ohms ±5%, 1/4 w.
	C57	19A700015P32	Teflon/mica: 130 pf ±5%, 250 VDCW.	1	R12 and	19C320212P1	Shunt resistor.
	C61	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.	Ì	R13		
	C62	19A116795P39J	Metallized teflon: 39 pf ±5%, 250 VDCW.		т1	19A129574G1	
$\ \ $	C63	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.		11	19812957401	Coil.
	C64*	19B209723P5	Tantalum: 15 µf ±20%, 20 VDCW. Added by REV A.		W1		(Part of Printed Board 19D424265P1).
			DIODES AND RECTIFIERS		thru W6		
	CR1 and	19A116052P2	Hot carrier: Forward drop .410 volts max.		W7	19A137006P2	Jumper.
	CR2				₩8	19A137006P1	Jumper.
					₩9		(Part of Printed Board 19D424265Pl).
	J210	19B219374G1	Connector: 9 contacts.		W30 thru	19A136950P1	Strap,
					W32		
	Ll	19B227929P1	Coil.		Z1	19A137330G1	Filter. Includes:
	L2	19A137008P1	Coil.		thru Z3		
	L3	19A129773G1	Coil.		LI	19A129773G5	Coil.
	1.4	19A129575P1	Coil.		Rl	3R78P100J	Resistor, composition: 10 ohms $\pm 5\%$, 1 w.
	L5	19A129561P2	Coil.		Z4	19A137332G1	Network, load. Includes:
	L6 and L7	19A137007P1	Co11.		and Z5		
П	rs .	19A129773G1	Coil.		Cl	7489162P13	Capacitor, silver mica: 27 pf $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15.
	L9		(Part of Printed Board 19D424265Pl).		Rl	3R79P240J	Resistor, composition: 24 ohms ±5%, 2 w.
	L10	19A136716P2	Coil.	-			
	L11	19A137008P2	Coil.				MISCELLANEOUS
П	L12 and L13	19A137007P1	Coil.	1		19B232325P1	Shield. (Located around R6 & R7). Shield. (Located between C4 & C15).
	L14	19A129773G1	Coil.			19A137331P1	Shield. (Located between C4 & C15).
Ш	L15		(Part of Printed Board 19D424265P1).	1			
П	L16	19A136716P2	Coil.				
	L17	19A137008P2	Coil.				
	L18 thru L20	19A700024P13	Coil, RF: 1.00 μh ±10%, 1.00 ohms DC res max.				
	L21	19A129561P3	Coil.				
	L22	19A136533P2	Coil.				
	L23 and L24	19A136907P2	Coil.				
	L25 and L26	19B209420P101	Coil, RF: 0.10 μh $\pm 10\%$, 0.08 ohms DC res max; sim to Jeffers 4416-1K.				
			TRANSISTORS				
	Q1	19A134340P4	Silicon, NPN: BVCBO 36 v min, 100 w min at 12.5 v				
	Q2 and	19A134387PI	Silicon, NPN: BVCBO 36 v min, 70 watt, 12.5 v.				
	Q3						
	and the state of t						
	Linearing						





SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
C43	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.			RESISTORS
C44	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim	RI	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
		to RMC Type JF Discap.	R3	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
C45 thru	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R5	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
C47 C48 thru	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R6 and R7	19All6559Pl01	Variable, cermet: 1K ohms ±20%, 0.5 w; sim to CTS Series 360.
C54		to fine Type of Biscap.	R8	19A700106P32	Composition: 51 ohms ±5%, 1/4 w.
C55	19A134202P15	Tantalum: 6.8 µf ±20%, 35 VDCW.	R9	19A700106P35	Composition: 68 ohms ±5%, 1/4 w.
C56	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.	R12	19C320212P1	
C57	19A700015P32	Teflon/mica: 130 pf ±5%, 250 VDCW.	and R13	19032021291	Shunt resistor.
C61	19A700015P37	Teflon/mica: 220 pf ±5%, 250 VDCW.	RIS .		The state of the s
C62	19A116795P39J	Metallized teflon: 39 pf ±5%, 250 VDCW.			
C63	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	T1	19A129574G1	Coil.
C64*	19B209723P5	Tantalum: 15 µf ±20%, 20 VDCW. Added by REV A.	w1		(Part of Printed Board 19D424265P1).
		DIODES AND DESTINIBLE	thru W6	l	(Fait of Filitted Board 195424205F1).
CD)	10431605000	DIODES AND RECTIFIERS	W7	19A137006P2	Tuesco v
CR1 and	19A116052P2	Hot carrier: Forward drop .410 volts max.			Jumper.
CR2			W8	19A137006P1	Jumper.
		JACKS AND RECEPTACLES	₩9		(Part of Printed Board 19D424265P1).
J210	19B219374G1	Connector: 9 contacts.	W30 thru W32	19A136950P1	Strap.
		INDUCTORS			
Ll	19B227929P1	Coil.	21	19A137330G1	Filter. Includes:
L2	19A137008P1	Coil.	thru Z3		
L3	19A129773G1	Coil.	Ll	19A129773G5	Coil.
1.4	19A129575Pl	Coil.	R1	3R78P100J	Resistor, composition: 10 ohms ±5%, 1 w.
L5	19A129561P2	Coil.	Z4	19A137332G1	Network, load. Includes:
L6 and L7	19A137007P1	Coil.	and Z5		
L8	19A129773G1	Coil.	C1	7489162P13	Capacitor, silver mica: 27 pf ±5%, 500 VDCW; to Electro Motive Type DM-15.
L9		(Part of Printed Board 19D424265P1).	R1	3R79P240J	Resistor, composition: 24 ohms ±5%, 2 w.
L10	19A136716P2	Coil.			
Lll	19A137008P2	Coil.			MISCELLANEOUS
L12	19A137007Pl	Coil.		19B232325P1	Shield. (Located around R6 & R7).
and L13				19A137331P1	Shield. (Located between C4 & C15).
L14	19A129773G1	Coil.			
L15		(Part of Printed Board 19D424265P1).			
L16	19A136716P2	Coil.			
L17	19A137008P2	Coil.			
L18 thru L20	19A700024P13	Coil, RF: 1.00 μh ±10%, 1.00 ohms DC res max.			
L21	19A129561P3	Coil.			
L22	19A136533P2	Coil.			
L23 and	19A136907P2	Coil.			
L24 L25 and L26	198209420P101	Coil, RF: 0.10 μh ±10%, 0.08 ohms DC res max; sim to Jeffers 4416-1K.			
		TRANSISTORS			
Q1	19A134340P4	Silicon, NPN: BYCBO 36 v min, 100 w min at 12.5 v			
Q2 and Q3	19A134387P1	Silicon, NPN: BYCBO 36 v min, 70 watt, 12.5 v.			

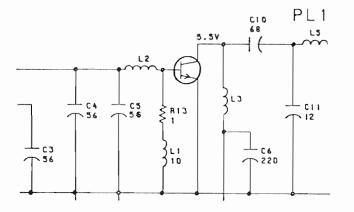
PRODUCTION CHANGES

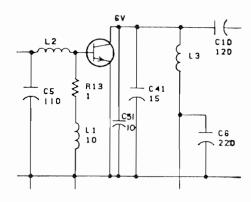
Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A 110 Watt Power Amplifier 19D424266G1, A206
 - To improve operation of power control circuit. Added C64.
- REV. B To delete components not required with improved power control IC. Deleted ${\rm C64}$.
- REV. A 10 Watt Driver 19D424309G1

To improve operation when Solid State Scientific, Inc. (SSS) transistors are used for Q201. Delete C39. Change C11 and add L2.

- REV. B To improve operation when Communication Transistor Corp. (CTC) transistors are used for Q201. Delete C39, add L2. Changed C11 and added C51.
- REV. C To improve operation when TRW transistors are used for Q201.
 Deleted C51 and L2. Added C39 and changed C11.





- REV. D To improve performance. Changed R5.
- REV. E To improve operation of power control circuit. Added C51.
- REV. F To delete components not required with improved Power Control IC. Deleted C51.